
October 22 (Thu.), 2026

[Oral 10] CMP Fundamentals

09:45-11:10

International Conference Hall (B1F)

● Session Chair: Xinchun Lu (Tsinghua Univ., China)

09:45-10:10 **[Invited]** Research on Atomic-scale Tribochemistry Underlying Wafer-Scale

[Oral 10-1] Global Planarization of Advanced Integrated Circuits

Lifei Zhang, Xinchun Lu (Tsinghua Univ., China), Knut Christoph Gottfried, and Jinji Luo-Hofmann (Fraunhofer Inst. for Electronic Nano Systems ENAS, Germany)

10:10-10:30 Clarification of Polishing Mechanism Focusing on Abrasive Particle Behavior

★[Oral 10-2] in CMP - Relationship between Abrasive Particle Behavior and Pad Surface Topography in Micro Replicated CMP Pad -

Haruto Kurokawa, Yoji Oyama, Syuhei Kurokawa, Terutake Hayashi, Keisuke Osawa (Kyushu Univ., Japan), Hirokuni Hiyama, Yutaka Wada, Naoyuki Handa, and Syuntaro Hayashi (Ebara Corp., Japan)

10:30-10:50 Micro-Structured Pads for High-MRR and Low-Damage Oxide Chemical

★[Oral 10-3] Mechanical Polishing

Seounghee Yun, Hyun Jun Ryu, Hyeongmin Je, and Sanha Kim (KAIST, Korea)

10:50-11:10 Physics-Informed Friction Coefficient Distribution Modeling for Material

★[Oral 10-4] Removal Rate Prediction in Chemical Mechanical Polishing

Sho Hirono (Kobe Univ., Japan), Chihiro Mitani (Chuo Univ., Japan), Takumi Sato, Kodai Hirano (Ebara Corp., Japan), and Norikazu Suzuki (Kobe Univ., Japan)